

Errata SLG47105 CE-GP-003

Abstract

This document contains the known errata for SLG47105 and the recommended workarounds.



1 Information

Package(s)	20-pin STQFN: 2 mm x 3 mm x 0.55 mm, 0.4 mm pitch
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2 Errata Summary

Table 1: Errata Summary

Issue #	Issue Title			
1	Dependence of Current Consumption on I2C Read/Write Operation			
2	Shifted Rising Edge of the Cycle when the Fast Decay is Applied			

3 Errata Details

3.1 Dependence of Current Consumption on I²C Read/Write Operation

3.1.1 Effect

Chip Current

3.1.2 Conditions

When I²C Read/Write operation stops at certain addresses.

3.1.3 Technical Description

Read/Write operation at certain addresses via I²C can cause significant current consumption increase. The amount of current drawn by the chip is highly dependent on V_{DD} voltage that is applied to the IC, please see Table 2.

Table 2: Chip Current Consumption

V _{DD}	Current Consumption After I ² C Interaction with Problematic Addresses	Normal Current Consumption After I ² C Interaction
2.3 V	39-150 μΑ	0.033 μΑ
2.5 V	45-93 μA	0.033 μΑ
3.3 V	84-339 μA	0.035 μΑ
4.0 V	121-488 μΑ	0.035 μΑ
5.0 V	177-710 μΑ	0.040 μΑ
5.5 V	206-822 μΑ	0.040 μΑ

I²C Address pointer increases after the stop of I²C operation. So, in case when Read/Write command stops right before the problematic address, the current consumption increase will appear.

Value of an excess current changes relative to the value of a register being read/written. Most likely, current consumption will increase in the case of reading «1» from the problematic register or writing «0» to it.



3.1.4 Workaround

The best workaround is not to stop the I²C Read/Write operation on the problematic addresses (for example, instead of reading just 0x4E and 0x4F addresses, the Sequential Read Command should include addresses 0x4E, 0x4F, 0x50). This helps to keep an increase time as short as possible.

Also, the problem could be solved by initiating another Read/Write operation with an unaffected address. For the known problematic addresses refer to Table 3.

Table 3: Known Problematic Addresses

Address	0x48	0x49	0x4A	0x4B	0x4D	0x4E	0x4F	0x89
Operation	R/W	R/W	R/W	R/W	R/W	R/W	W	W

Address	0x8A	0x8B	0xA4	0xA5	0xF9	0xFB	0xFC	
Operation	R	W	R/W	R/W	W	R/W	W	

3.2 Shifted Rising Edge of the Cycle when the Fast Decay is Applied

3.2.1 **Effect**

High Side Pin

3.2.2 Conditions

When Fast Decay mode is applied.

3.2.3 Technical Description:

In the Fast Decay mode, the negative voltage, created by the inductive load on the HV_GPO_HD pin, discharges the internal Charge Pump due to the parasitic p-n junction. Because of this, the Rising Edge on the High Side pin shifts. The duration of the shift depends on the Duty Cycle, the High Side input voltage (V_{DD2}), and the PWM frequency.

For example, the PWM Duty Cycle values higher than 75 % in a combination with V_{DD2} voltage lower than 3.75 V, and the Fast Decay settings applied can cause this problem, please see Figure 1 and Figure 2.

Note: HV GPO_0/1 are set to H-Bridge, Slow Slew Rate, Mode Control: PH-EN. In this case, EN is «HIGH», DECAY MODE Input is «LOW» (Fast Decay).



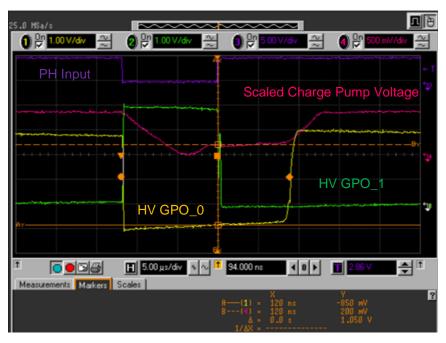


Figure 1: Shifted Rising Edge (V_{DD2} = 3.0 V, Fast Decay, PWM = 75+ %)

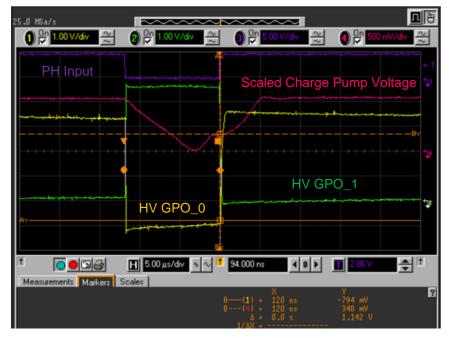


Figure 2: Discharge of the Internal Charge Pump (V_{DD2} = 3.75 V, Fast Decay, PWM = 75+ %)

3.2.4 Workaround:

The best way to exclude a possibility of such a malfunction is to use the Slow Decay option for the H-Bridge instead of the Fast Decay. No evidence of improper behavior has been discovered when V_{DD2} is higher than 3.75 V and the Fast Decay settings are applied. The chip is not affected by this problem when the load is resistive, because the negative voltage will appear on a pin only when the inductive load discharges.



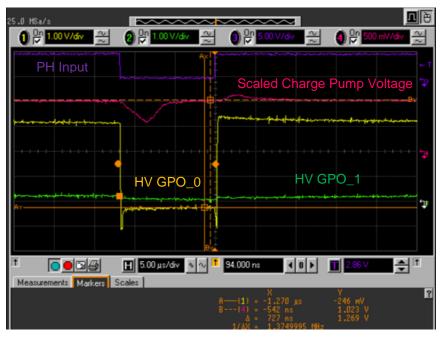


Figure 3: Rising Edge is Not Shifted (V_{DD2} = 3.75 V, Slow Decay, PWM = 75+ %)

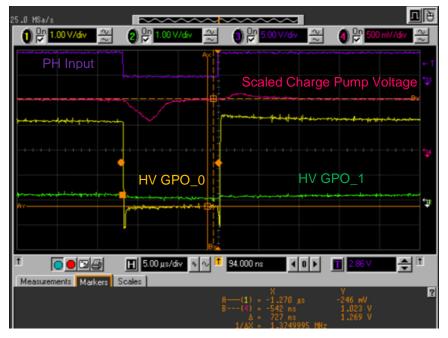


Figure 4: Low V_{DD2} Voltage Operation (V_{DD2} = 2.75 V, Slow Decay, PWM = 75+ %)



Document Revision History

Revision	Date	Description	
1.1	24-Jun-2020	Updated according to new Dialog's format	



Status Definitions

Status	Definition
DRAFT	The content of this document is under review and subject to formal approval, which may result in modifications or additions.
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